

IRF9540, IRF9541, IRF9542, IRF9543, RF1S9540, RF1S9540SM

-15A and -19A, -80V and -100V, 0.20 and 0.30 Ohm,
 P-Channel Power MOSFETs

July 1998

Features

- -15A and -19A, -80V and -100V
- $r_{DS(ON)} = 0.20\Omega$ and 0.30Ω
- Single Pulse Avalanche Energy Rated
- SOA is Power Dissipation Limited
- Nanosecond Switching Speeds
- Linear Transfer Characteristics
- High Input Impedance
- Related Literature
 - TB334 "Guidelines for Soldering Surface Mount Components to PC Boards"

Ordering Information

PART NUMBER	PACKAGE	BRAND
IRF9540	TO-220AB	IRF9540
IRF9541	TO-220AB	IRF9541
IRF9542	TO-220AB	IRF9542
IRF9543	TO-220AB	IRF9543
RF1S9540	TO-262AA	RF1S9540
RF1S9540SM	TO-263AB	RF1S9540

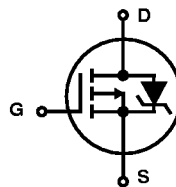
NOTE: When ordering, use the entire part number. Add the suffix 9A to obtain the TO-263AB variant in the tape and reel, i.e., RF1S9540SM9A.

Description

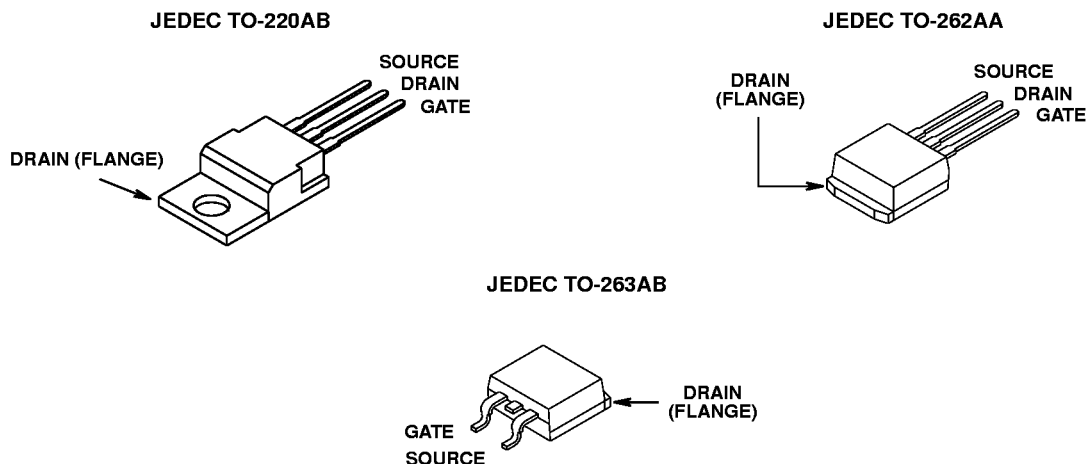
These are P-Channel enhancement mode silicon gate power field effect transistors. They are advanced power MOSFETs designed, tested, and guaranteed to withstand a specified level of energy in the breakdown avalanche mode of operation. All of these power MOSFETs are designed for applications such as switching regulators, switching converters, motor drivers, relay drivers, and drivers for high power bipolar switching transistors requiring high speed and low gate drive power. They can be operated directly from integrated circuits.

Formerly Developmental Type TA17521.

Symbol



Packaging



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Absolute Maximum Ratings $T_C = 25^{\circ}\text{C}$, Unless Otherwise Specified

	IRF9540, RF1S9540, RF1S9540SM	IRF9541	IRF9542	IRF9543	UNITS
Drain to Source Voltage (Note 1) V_{DS}	-100	-80	-100	-80	V
Drain to Gate Voltage ($R_{GS} = 20\text{k}\Omega$) (Note 1) V_{DGR}	-100	-80	-100	-80	V
Continuous Drain Current I_D	-19	-19	-15	-15	A
$T_C = 100^{\circ}\text{C}$ I_D	-12	-12	-10	-10	A
Pulsed Drain Current (Note 3) I_{DM}	-76	-76	-60	-60	A
Gate to Source Voltage V_{GS}	± 20	± 20	± 20	± 20	V
Maximum Power Dissipation (Figure 1) P_D	150	150	150	150	W
Linear Derating Factor (Figure 1)	1	1	1	1	W/ $^{\circ}\text{C}$
Single Pulse Avalanche Energy Rating (Note 4) E_{AS}	960	960	960	960	mJ
Operating and Storage Temperature T_J, T_{STG}	-55 to 175	-55 to 175	-55 to 175	-55 to 175	$^{\circ}\text{C}$
Maximum Temperature for Soldering					
Leads at 0.063in (1.6mm) from Case for 10s T_L	300	300	300	300	$^{\circ}\text{C}$
Package Body for 10s, See Techbrief 334 T_{pkg}	260	260	260	260	$^{\circ}\text{C}$

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

NOTE:

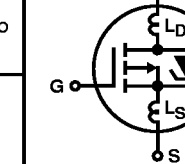
1. $T_J = 25^{\circ}\text{C}$ to 150°C .

Electrical Specifications $T_C = 25^{\circ}\text{C}$, Unless Otherwise Specified

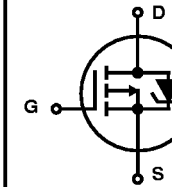
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Drain to Source Breakdown Voltage IRF9540, IRF9542, RF1S9540, RF1S9540SM	BV_{DSS}	$I_D = -250\mu\text{A}$, $V_{GS} = 0\text{V}$ (Figure 10)	-100	-	-	V
IRF9541, IRF9543			-80	-	-	V
Gate to Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}$, $I_D = -250\mu\text{A}$	-2	-	-4	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = \text{Rated } BV_{DSS}$, $V_{GS} = 0\text{V}$	-	-	-25	μA
		$V_{DS} = 0.8 \times \text{Rated } BV_{DSS}$, $V_{GS} = 0\text{V}$ $T_C = 125^{\circ}\text{C}$	-	-	-250	μA
On-State Drain Current (Note 2) IRF9540, IRF9541, RF1S9540, RF1S9540SM	$I_{D(ON)}$	$V_{DS} > I_{D(ON)} \times r_{DS(ON)} \text{ MAX}$, $V_{GS} = -10\text{V}$	-19	-	-	A
IRF9542, IRF9543			-15	-	-	A
Gate to Source Leakage Current	I_{GSS}	$V_{GS} = \pm 20\text{V}$	-	-	± 100	nA
Drain to Source On Resistance (Note 2) IRF9540, IRF9541, RF1S9540, RF1S9540SM	$r_{DS(ON)}$	$I_D = -10\text{A}$, $V_{GS} = -10\text{V}$ (Figures 8, 9)	-	0.15	0.20	Ω
IRF9542, IRF9543			-	0.22	0.30	Ω
Forward Transconductance (Note 2)	g_{fs}	$V_{DS} > I_{D(ON)} \times r_{DS(ON)} \text{ MAX}$, $I_D = -6\text{A}$ (Figure 12)	5	7	-	S
Turn-On Delay Time	$t_{d(ON)}$	$V_{DD} = -50\text{V}$, $I_D \approx 19\text{A}$, $R_G = 9.1\Omega$, $R_L = 2.3\Omega$, $V_{GS} = -10\text{V}$, (Figures 17, 18) MOSFET Switching Times are Essentially Independent of Operating Temperature	-	16	20	ns
Rise Time	t_r		-	65	100	ns
Turn-Off Delay Time	$t_{d(OFF)}$		-	47	70	ns
Fall Time	t_f		-	28	70	ns
Total Gate Charge (Gate to Source + Gate to Drain)	$Q_{g(TOT)}$	$V_{GS} = -10\text{V}$, $I_D = -19\text{A}$, $V_{DS} = 0.8 \times \text{Rated } BV_{DSS}$, $I_{g(REF)} = -1.5\text{mA}$ (Figures 14, 19, 20) Gate Charge is Essentially Independent of Operating Temperature	-	70	90	nC
Gate to Source Charge	Q_{gs}		-	14	-	nC
Gate to Drain "Miller" Charge	Q_{gd}		-	56	-	nC

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Electrical Specifications $T_C = 25^\circ\text{C}$, Unless Otherwise Specified (Continued)

PARAMETER	SYMBOL	TEST CONDITIONS		MIN	TYP	MAX	UNITS
Input Capacitance	C _{ISS}	V _{DS} = -25V, V _{GS} = 0V, f = 1MHz (Figure 11)		-	1100	-	pF
Output Capacitance	C _{OSS}			-	550	-	pF
Reverse Transfer Capacitance	C _{RSS}			-	250	-	pF
Internal Drain Inductance	L _D	Measured From the Contact Screw on Tab to the Center of Die	Modified MOSFET Symbol Showing the Internal Devices Inductances 	-	3.5	-	nH
		Measured From the Drain Lead, 6mm (0.25in) from Package to the Center of Die		-	4.5	-	nH
Internal Source Inductance	L _S	Measured From the Source Lead, 6mm (0.25in) From Package to Source Bonding Pad			-	7.5	-
Thermal Resistance Junction to Case	R _{θJC}			-	-	1	°C/W
Thermal Resistance Junction to Ambient	R _{θJA}	Typical Socket Mount		-	-	62.5	°C/W

Source to Drain Diode Specifications

PARAMETER	SYMBOL	TEST CONDITIONS		MIN	TYP	MAX	UNITS
Continuous Source to Drain Current	I _{SD}	Modified MOSFET Symbol Showing the Integral Reverse P-N Junction Diode		-	-	-19	A
Pulse Source to Drain Current (Note 3)	I _{SDM}			-	-	-76	A
Source to Drain Diode Voltage (Note 2)	V _{SD}	T _C = 25°C, I _{SD} = -19A, V _{GS} = 0V (Figure 13)		-	-	-1.5	V
Reverse Recovery Time	t _{rr}	T _J = 150°C, I _{SD} = 19A, dI _{SD} /dt = 100A/μs		-	170	-	ns
Reverse Recovery Charge	Q _{RR}	T _J = 150°C, I _{SD} = 19A, dI _{SD} /dt = 100A/μs		-	0.8	-	μC

NOTES:

- Pulse test: pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$.
- Repetitive rating: pulse width limited by maximum junction temperature. See Transient Thermal Impedance curve (Figure 3).
- $V_{DD} = 25\text{V}$, starting $T_J = 25^\circ\text{C}$, $L = 4\text{mH}$, $R_G = 25\Omega$, peak $I_{AS} = 19\text{A}$. (Figures 15, 16).

Typical Performance Curves Unless Otherwise Specified

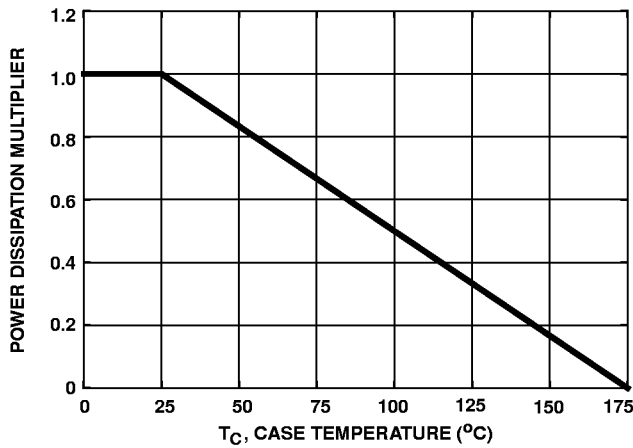


FIGURE 1. NORMALIZED POWER DISSIPATION vs CASE TEMPERATURE

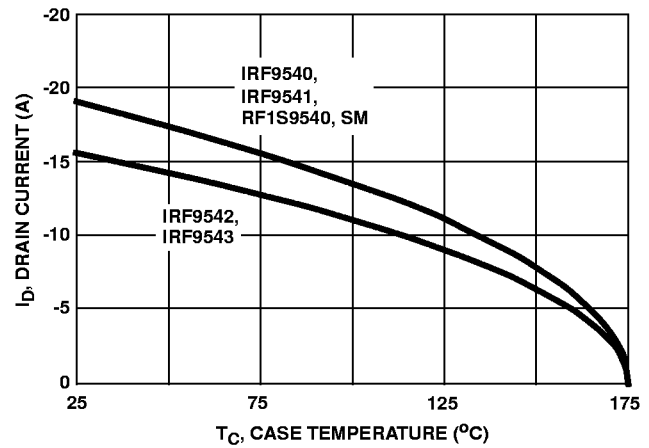


FIGURE 2. MAXIMUM CONTINUOUS DRAIN CURRENT vs CASE TEMPERATURE

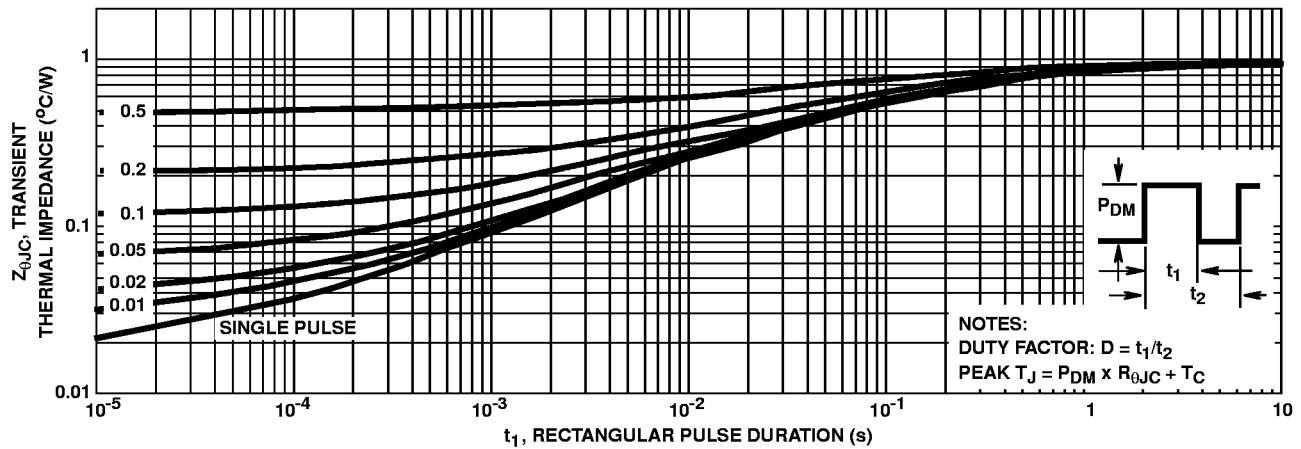


FIGURE 3. NORMALIZED MAXIMUM TRANSIENT THERMAL IMPEDANCE

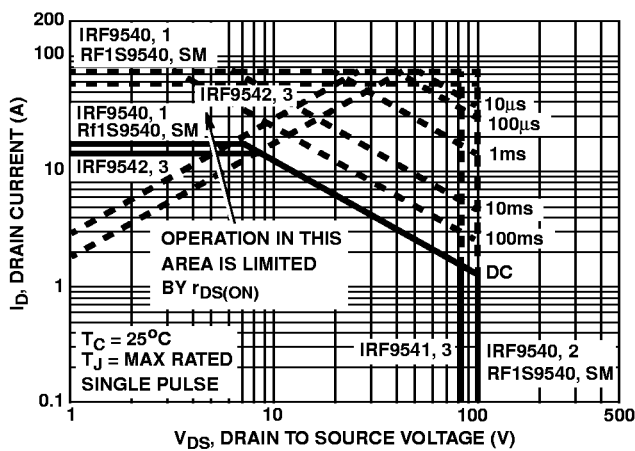


FIGURE 4. FORWARD BIAS SAFE OPERATING AREA

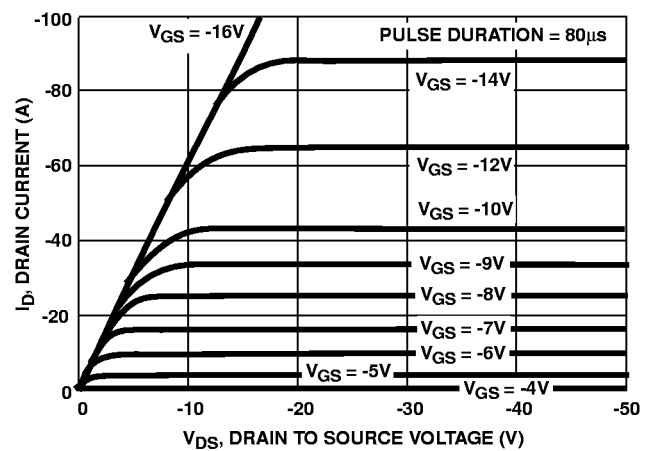


FIGURE 5. OUTPUT CHARACTERISTICS

Typical Performance Curves Unless Otherwise Specified (Continued)

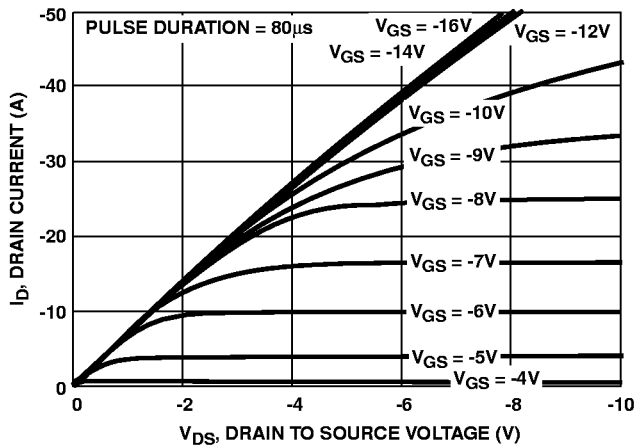


FIGURE 6. SATURATION CHARACTERISTICS

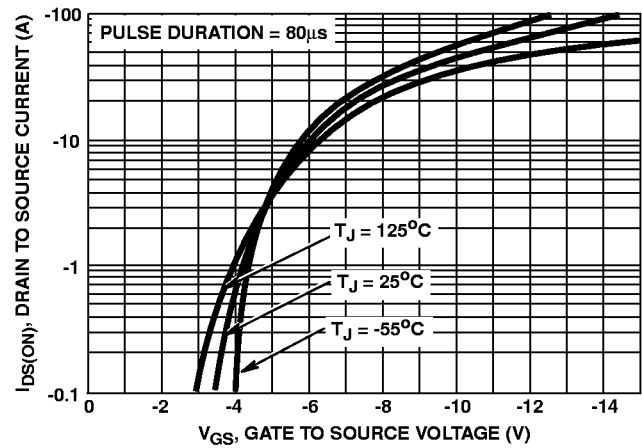
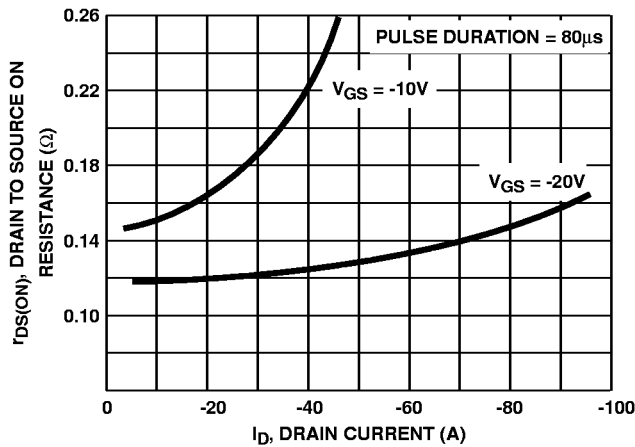


FIGURE 7. TRANSFER CHARACTERISTICS



NOTE: Heating effect of 2μs pulse is minimal.

FIGURE 8. DRAIN TO SOURCE ON RESISTANCE vs GATE VOLTAGE AND DRAIN CURRENT

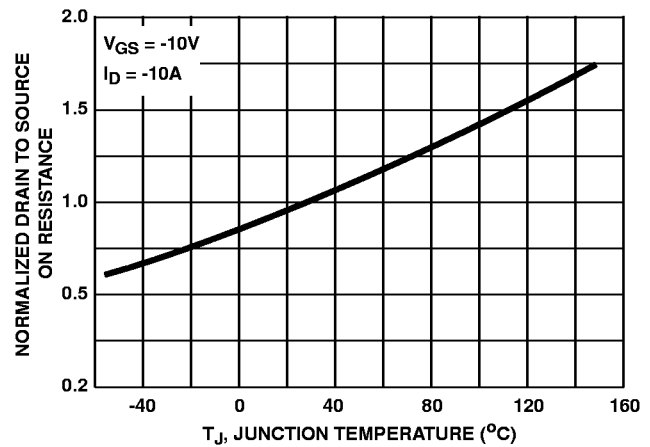


FIGURE 9. NORMALIZED DRAIN TO SOURCE ON RESISTANCE vs JUNCTION TEMPERATURE

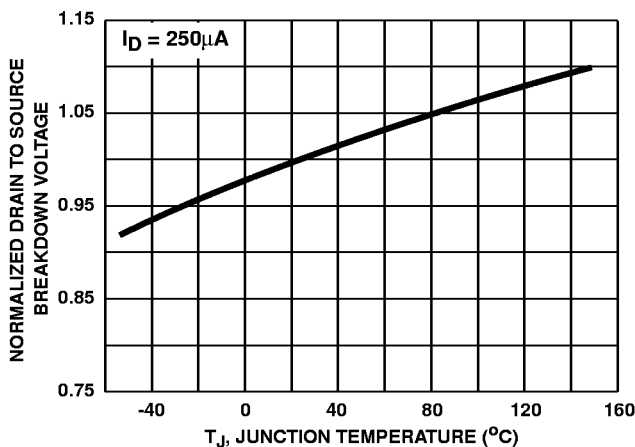


FIGURE 10. NORMALIZED DRAIN TO SOURCE BREAKDOWN VOLTAGE vs JUNCTION TEMPERATURE

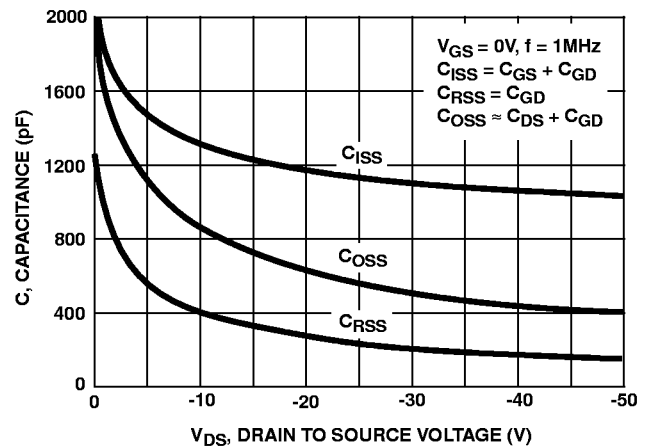


FIGURE 11. CAPACITANCE vs DRAIN TO SOURCE VOLTAGE

Typical Performance Curves Unless Otherwise Specified (Continued)

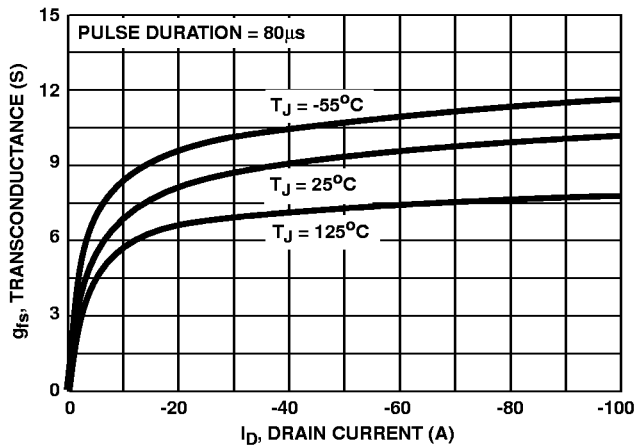


FIGURE 12. TRANSCONDUCTANCE vs DRAIN CURRENT

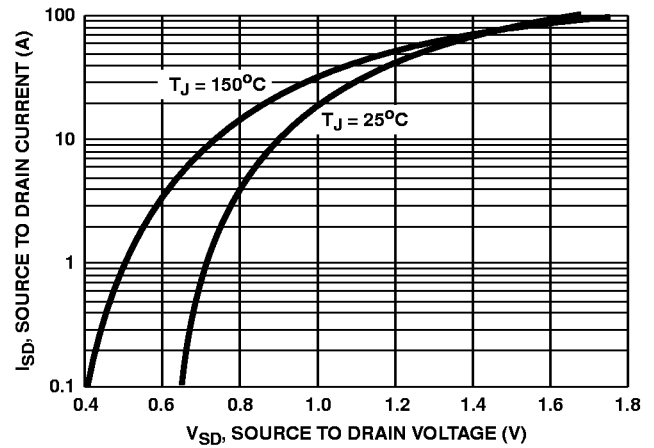


FIGURE 13. SOURCE TO DRAIN DIODE VOLTAGE

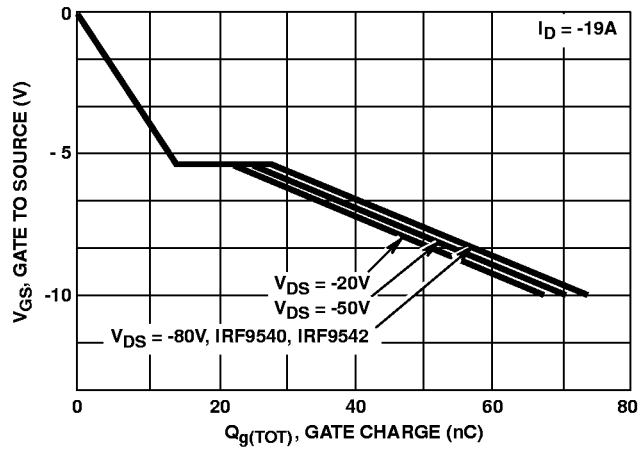


FIGURE 14. GATE TO SOURCE VOLTAGE vs GATE CHARGE

